

BSR50

NPN Darlington Transistor

- This device designed for applications requiring extremely high gain at collector currents to 0.5A.
- Sourced from Process 06.



1. Emitter 2. Collector 3. Base

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_A =25°C unless otherwise noted

| Symbol | Parameter | Ratings | Units | |
|-----------------------------------|---------------------------|-----------|-------|--|
| V_{CEO} | Collector-Emitter Voltage | 45 | V | |
| V_{CBO} | Collector-Base Voltage | 60 | V | |
| V_{EBO} | Emitter-Base Voltage | 5 | V | |
| I _C | Collector Current | 1.5 | Α | |
| T _J , T _{STG} | Storage Temperature | -55 ~ 150 | °C | |

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{\textbf{A}} = 25 ^{\circ} \textbf{C} \ \, \textbf{unless otherwise noted}$

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|---------------------------------------|---|----------------|------|------------|-------|
| BV _{CEO} | Collector-Emitter Breakdown Voltage * | $I_C = 10 \text{mA}, I_B = 0$ | 45 | | | V |
| BV _{CBO} | Collector-Base Breakdown Voltage | $I_C = 100\mu A, I_B = 0$ | 60 | | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_E = 100 \mu A, I_C = 0$ | 5 | | | V |
| I _{CBO} | Collector Cut-off Current | $V_{CB} = 45V, I_{E} = 0$ | | | 50 | nA |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = 4.0V, I_{C} = 0$ | | | 50 | nA |
| h _{FE} | DC Current Gain | V _{CE} = 10V, I _C = 150mA V _{CE} = 10V, I _C = 0.5A | 1,000 2,000 | | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | $I_C = 500 \text{mA}, I_B = 500 \mu \text{A}$ $I_C = 1.0 \text{A}, I_B = 4.0 \text{mA}$ | | | 1.3 1.6 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | $I_C = 500 \text{mA}, I_B = 500 \mu \text{A}$ $I_C = 1.0 \text{mA}, I_B = 4.0 \text{mA}$ | | | 0.9 2.2 | V |

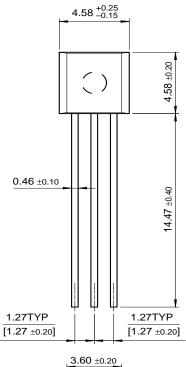
Thermal Characteristics $T_A=25$ °C unless otherwise noted

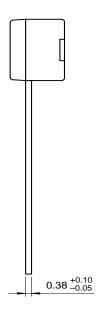
| Symbol | Parameter | Max. | Units |
|-----------------|---|------|-------|
| P _D | Total Device Dissipation 625 | | mW |
| | Derate above 25°C | 5.0 | mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 83.3 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 200 | °C/W |

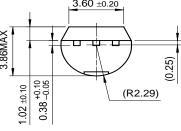
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Package Dimensions

TO-92







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